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April 2014

FDY102PZ

Single P-Channel (-1.5 V) Specified PowerTrench® MOSFET

-20 V, **-0.83** A, **0.5** Ω

Features

- Max $r_{DS(on)} = 0.5 \Omega$ at $V_{GS} = -4.5 \text{ V}$, $I_D = -0.83 \text{ A}$
- Max $r_{DS(on)} = 0.7 \Omega$ at $V_{GS} = -2.5 \text{ V}$, $I_D = -0.70 \text{ A}$
- Max $r_{DS(on)} = 1.2 \Omega$ at $V_{GS} = -1.8 \text{ V}$, $I_D = -0.43 \text{ A}$
- Max $r_{DS(on)} = 1.8 \Omega$ at $V_{GS} = -1.5 \text{ V}$, $I_D = -0.36 \text{ A}$
- HBM ESD protection level = 1400 V (Note 3)
- RoHS Compliant

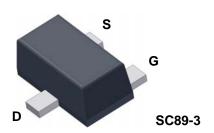


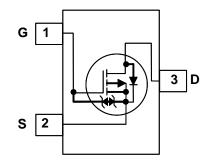
General Description

This Single P-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the $r_{DS(on)}@V_{GS}=-1.5~V$.

Application

■ Li-Ion Battery Pack





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DS}	Drain to Source Voltage		-20	V
V _{GS}	Gate to Source Voltage		±8	V
1	Drain Current -Continuous	(Note 1a)	-0.83	^
I _D	-Pulsed		-1.0	A
D	Power Dissipation	(Note 1a)	0.625	10/
P_{D}	Power Dissipation	(Note 1b)	0.446	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	200	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	280	*C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
E	FDY102PZ	SC89-3	7 "	8 mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, referenced to 25 °C		-11		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 5 \text{ V}, V_{DS} = 0 \text{ V}$			±0.5	μА

On Characteristics (Note 2)

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.4	-0.7	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, referenced to 25 °C		3		mV/°C
s Statio Drain to Source On Registance	$V_{GS} = -4.5 \text{ V}, I_D = -0.83 \text{ A}$		0.28	0.5		
		$V_{GS} = -2.5 \text{ V}, I_D = -0.70 \text{ A}$		0.36	0.7	
	Static Drain to Source On-Resistance	$V_{GS} = -1.8 \text{ V}, I_D = -0.43 \text{ A}$		0.47	1.2	Ω
r _{DS(on)}	Static Brain to Gource On-Acsistance	$V_{GS} = -1.5 \text{ V}, I_D = -0.36 \text{ A}$		0.62	1.8	32
		$V_{GS} = -4.5 \text{ V}, I_D = -0.83 \text{ A},$ $T_J = 125 ^{\circ}\text{C}$		0.39	0.85	
9 _{FS}	Forward Transconductance	$V_{DD} = -5 \text{ V}, I_{D} = -0.83 \text{ A}$		2		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 40 V V 0 V	100	135	pF
Coss	Output Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	23	35	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	18	30	pF

Switching Characteristics (Note 2)

t _{d(on)}	Turn-On Delay Time		3.5	10	ns
t _r	Rise Time	$V_{DD} = -10 \text{ V}, I_D = -0.83 \text{ A}$	2.9	10	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$	23	37	ns
t _f	Fall Time		13	23	ns
Q_q	Total Gate Charge	.,,	2.2	3.1	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = -10 \text{ V}, I_{D} = -0.83 \text{ A}$ $V_{GS} = -4.5 \text{ V}$	0.3		nC
Q_{qd}	Gate to Drain "Miller" Charge	v _{GS} = -4.5 v	0.6		nC

Drain-Source Diode Characteristics and Maximum Rating

I_S	Maximum Continuous Drain-Source Diode Forward Current				-0.52	Α
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -0.52 \text{ A}$ (Note 2)		-1.0	-1.2	V
t _{rr}	Reverse Recovery Time	$I_{\rm F} = -0.83 \text{ A, dI}_{\rm F}/{\rm dt} = 100 \text{ A/}\mu{\rm s}$		18	31	ns
Q _{rr}	Reverse Recovery Charge	$_{\text{IF}} = -0.83 \text{ A}, \text{ dif/dt} = 100 \text{ A/} \mu\text{s}$		3.8	10	nC

1. R_{0JA} is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.



a) 200 °C/W when mounted on a 1 in² pad of 2 oz copper.



b) 280 °C/W when mounted on a minimum pad of 2 oz copper.

 ^{2.} Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%
 3: The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25 °C unless otherwise noted

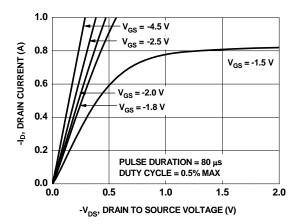


Figure 1. On Region Characteristics

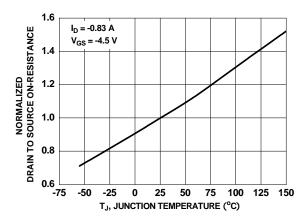


Figure 3. Normalized On Resistance vs Junction Temperature

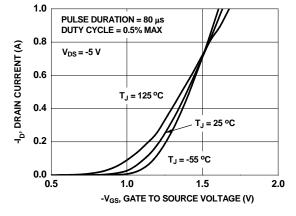


Figure 5. Transfer Characteristics

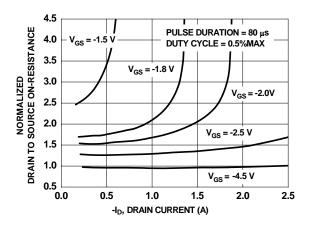


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

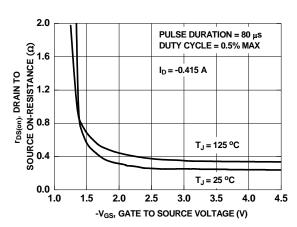


Figure 4. On-Resistance vs Gate to Source Voltage

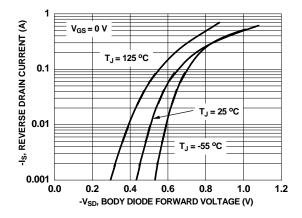


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

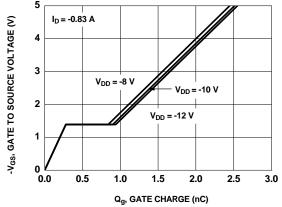


Figure 7. Gate Charge Characteristics

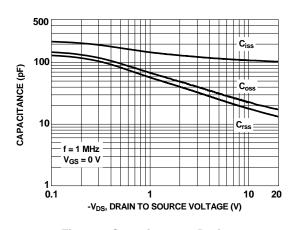


Figure 8. Capacitance vs Drain to Source Voltage

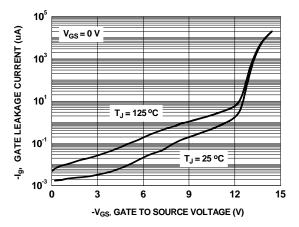


Figure 9. Gate Leakage Current vs Gate to Source Voltage

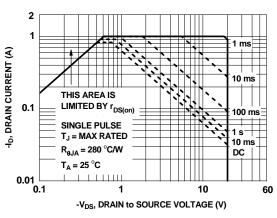


Figure 10. Forward Bias Safe Operating Area

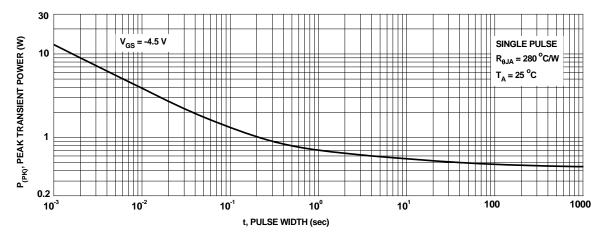


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

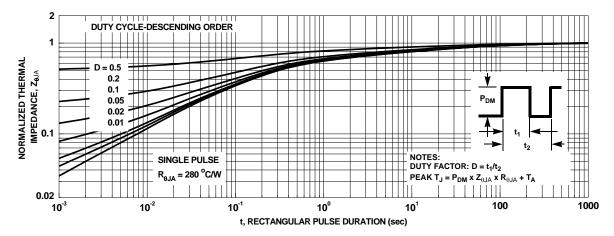
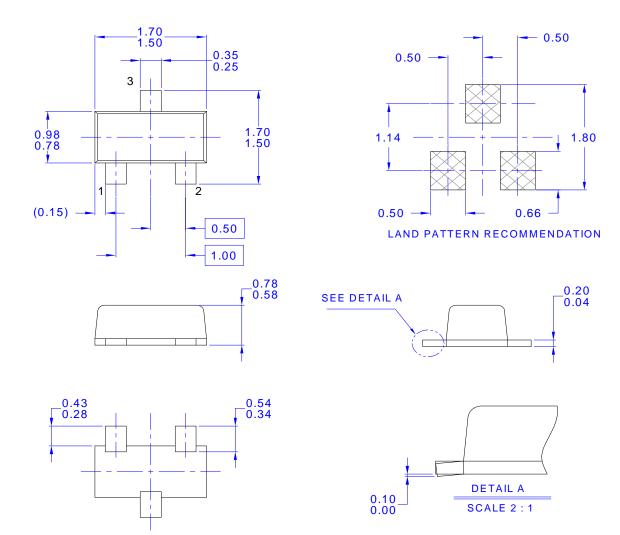


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO EIAJ
SC89 PACKAGING STANDARD.

- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

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